

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1509424	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 13:04
S2	75349	S1 and (field effect transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2005/05/04 13:05
S3	110	S2 and ((channel region) with source with drain with emitter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/04 13:07
S4	14	S3 and (gate dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/04 13:08
S5	14	S4 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/04 13:33
S6	4690	438/197,592,585,287,273,545, 965,236,316,335.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/04 13:35
S7	7	S6 and S3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/04 13:36
S8	5	S4 and S7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/05/04 13:37